TSM9435

-30V P-Channel Enhancement-Mode MOSFET

SOP-8

Pin assignment:
1. Source
2. Source
3. Source
4. Gate
5, 6, 7, 8. Drain

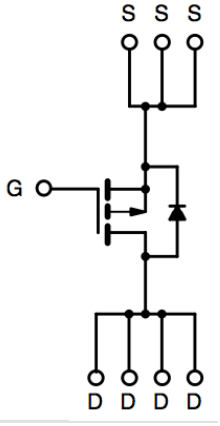
V_{DS} = -30V
$R_{DS\ (on)}$, Vgs @ -10V, Ids @ -5.3A =60mΩ
$R_{DS\ (on)}$, Vgs @ -4.5V, Ids @ -4.2A =90mΩ

Features

- ✧ Advanced trench process technology
- ✧ High density cell design for ultra low on-resistance
- ✧ Fully Characterized Avalanche Voltage and Current
- ✧ Improved Shoot-Through FOM

Block Diagram

P-Channel MOSFET



Ordering Information

Part No.	Packing	Package
TSM9435CS	Tape & Reel 2,500/per reel	SOP-8

Absolute Maximum Rating (Ta = 25 °C unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V_{DS}	-30V	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current,		I_D	-5.3	A
Pulsed Drain Current,		I_{DM}	-20	A
Maximum Power Dissipation	Ta = 25 °C	P_D	2.5	W
	Ta = 70 °C		1.3	
Operating Junction Temperature		T_J	+150	°C
Operating Junction and Storage Temperature Range		T_J, T_{STG}	- 55 to +150	°C

Thermal Performance

Parameter	Symbol	Limit	Unit
Junction to Foot (Drain) Thermal Resistance	Rθjf	30	°C/W
Junction to Ambient Thermal Resistance (PCB mounted)	Rθja	50	°C/W

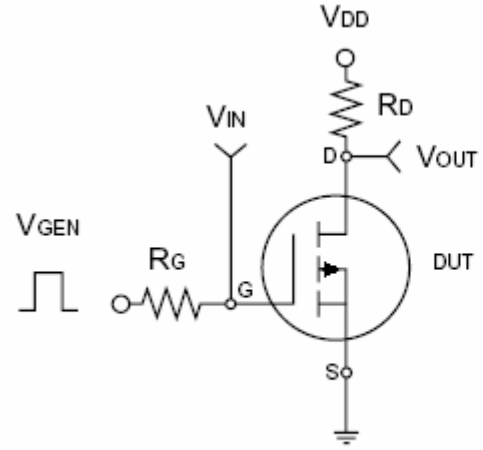
Note: Surface mounted on FR4 board t<=10sec.

Electrical Characteristics

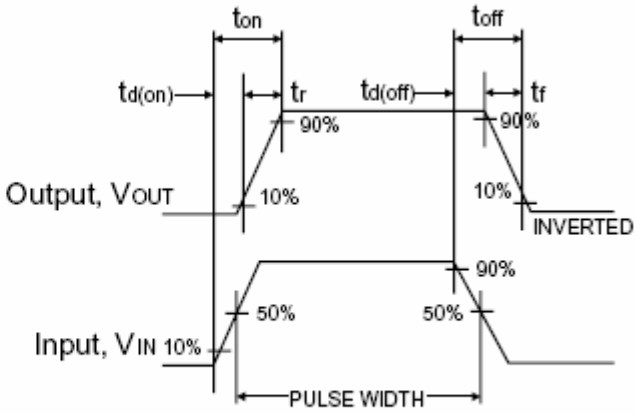
(Ta = 25 °C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Static						
Drain-Source Breakdown Voltage	V_{GS} = 0V, I_D = 250uA	BV_{DSS}	-30	--	--	V
Drain-Source On-State Resistance	V_{GS} = -10V, I_D = -5.3A	$R_{DS(ON)}$	--	50	60	mΩ
Drain-Source On-State Resistance	V_{GS} = -4.5V, I_D = -4.2A	$R_{DS(ON)}$	--	70	90	
Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250uA	$V_{GS(TH)}$	-1.0	-1.7	-3.0	V
Zero Gate Voltage Drain Current	V_{DS} = -24V, V_{GS} = 0V	I_{DSS}	--	--	-1.0	uA
Gate Body Leakage	V_{GS} = ±20V, V_{DS} = 0V	I_{GSS}	--	--	±100	nA
Forward Transconductance	V_{DS} = -15V, I_D = -5.3A	g_{fs}	4	7	--	S
Dynamic						
Total Gate Charge	V_{DS} = -15V, I_D = -5.3A, V_{GS} = -10V	Q_g	--	9.52	--	nC
Gate-Source Charge		Q_{gs}	--	3.43	--	
Gate-Drain Charge		Q_{gd}	--	1.71	--	
Turn-On Delay Time	V_{DD} = -15V, R_L = 15Ω, I_D = -1A, V_{GEN} = -10V, R_G = 6Ω	$t_{d(on)}$	--	10.8	--	nS
Turn-On Rise Time		t_r	--	2.33	--	
Turn-Off Delay Time		$t_{d(off)}$	--	22.53	--	
Turn-Off Fall Time		t_f	--	3.87	--	
Input Capacitance	V_{DS} = -15V, V_{GS} = 0V, f = 1.0MHz	C_{iss}	--	551.57	--	pF
Output Capacitance		C_{oss}	--	90.96	--	
Reverse Transfer Capacitance		C_{rss}	--	60.79	--	
Source-Drain Diode						
Max. Diode Forward Current		I_S	--	--	-1.9	A
Diode Forward Voltage	I_S = -5.3A, V_{GS} = 0V	V_{SD}	--	--	-1.3	V

Note : pulse test: pulse width <=300uS, duty cycle <=2%

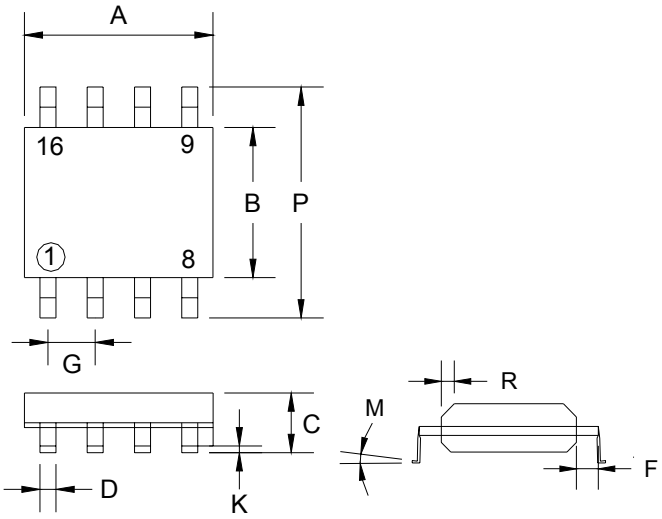


Switching Test Circuit



Switchin Waveforms

SOP-8 Mechanical Drawing



SOP-8 DIMENSION				
DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.80	5.00	0.189	0.196
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27 (typ)		0.05 (typ)	
K	0.10	0.25	0.004	0.009
M	0^o	7^o	0^o	7^o
P	5.80	6.20	0.229	0.244
R	0.25	0.50	0.010	0.019